

Silicon NPN Power Transistors

2SD1718

DESCRIPTION

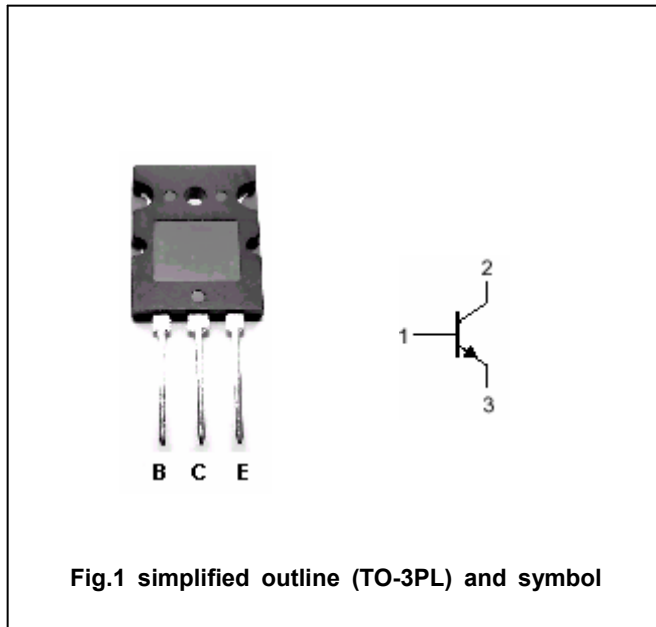
- With TO-3PL package
- Complement to type 2SB1163
- Excellent linearity of h_{FE}
- Wide area of safe operation (ASO)
- High transition frequency f_T

APPLICATIONS

- For high power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings($T_a=25^\circ C$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	180	V
V_{CEO}	Collector-emitter voltage	Open base	180	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		15	A
I_{CM}	Collector current-peak		25	A
P_C	Collector power dissipation		3.5	W
		$T_C=25^\circ C$	150	
T_j	Junction temperature		150	$^\circ C$
T_{stg}	Storage temperature		-55~150	$^\circ C$

Silicon NPN Power Transistors

2SD1718

CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEsat}	Collector-emitter saturation voltage	I _C =10A ; I _B =1A			2.5	V
V _{BE}	Base-emitter voltage	I _C =8A ; V _{CE} =5V			1.8	V
I _{CBO}	Collector cut-off current	V _{CB} =180V; I _E =0			50	μA
I _{EBO}	Emitter cut-off current	V _{EB} =3V; I _C =0			50	μA
h _{FE-1}	DC current gain	I _C =20mA ; V _{CE} =5V	20			
h _{FE-2}	DC current gain	I _C =1A ; V _{CE} =5V	60		200	
h _{FE-3}	DC current gain	I _C =8A ; V _{CE} =5V	20			
f _T	Transition frequency	I _C =0.5A ; V _{CE} =5V		20		MHz
C _{OB}	Collector output capacitance	f=1MHz; V _{CB} =10V		230		pF

◆ h_{FE-2} classifications

Q	S	P
60-100	80-160	100-200

Silicon NPN Power Transistors

2SD1718

PACKAGE OUTLINE

